大连理工大学
DALIAN UNIVERSITY OF TECHNOLOGY

打孔实验进展

徐瑞良

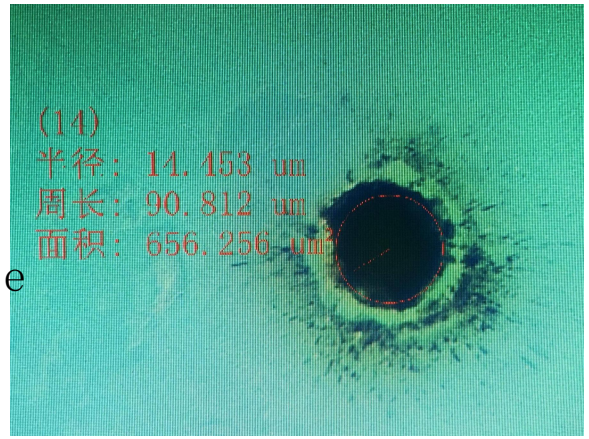
大连理工大学国家示范性微电子学院（筹）

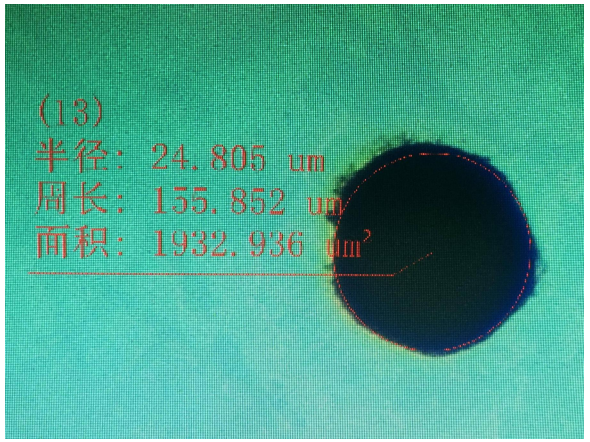
2021年7月20日

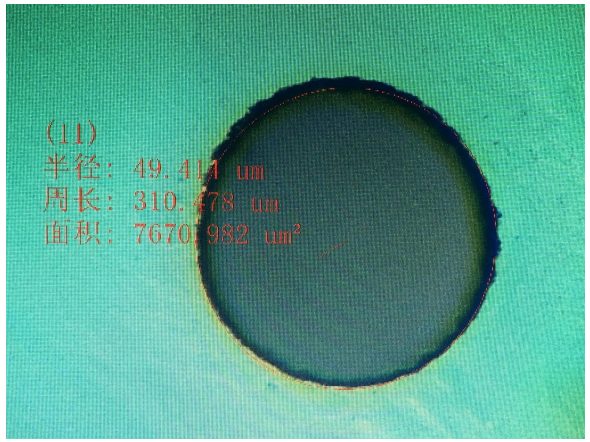
First Experiment

30 um | 50 um | 100 um

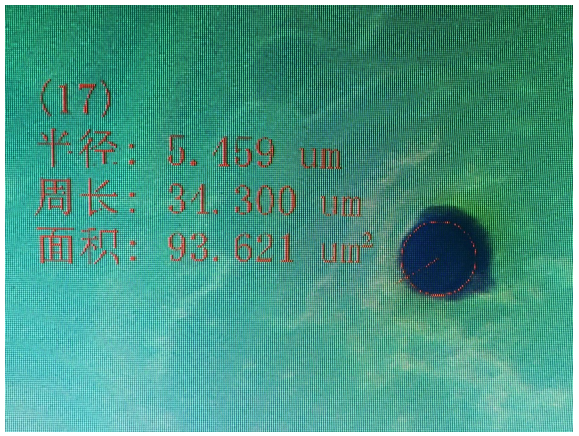
Incident surface

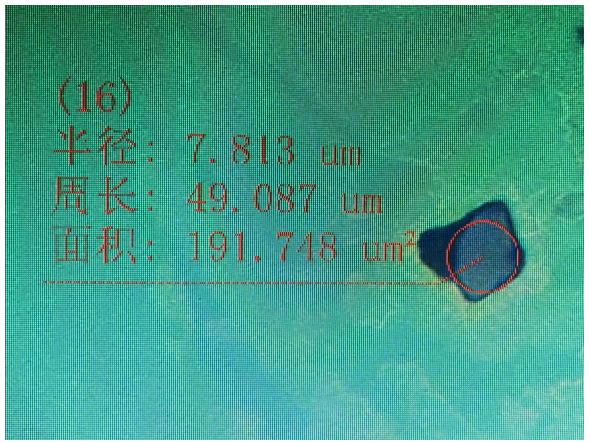


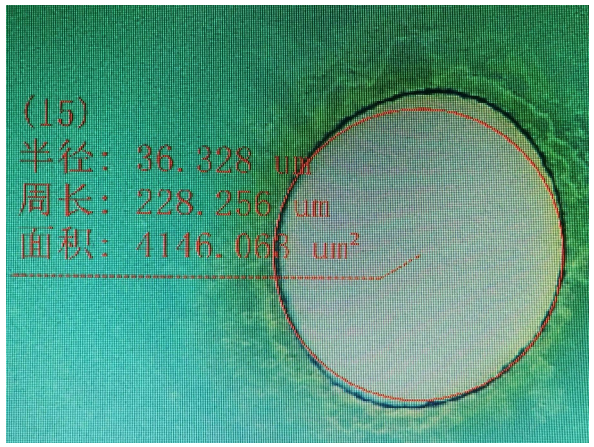




Exit surface

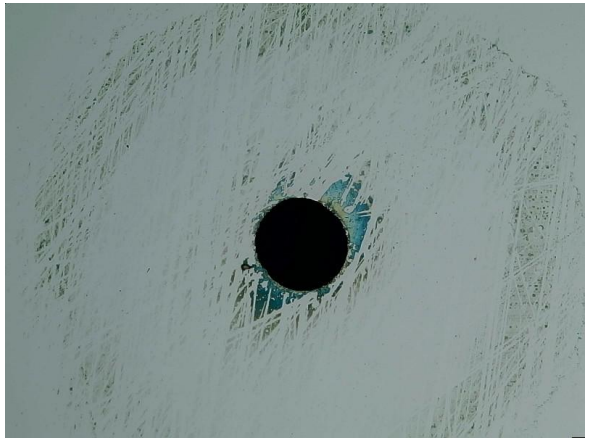
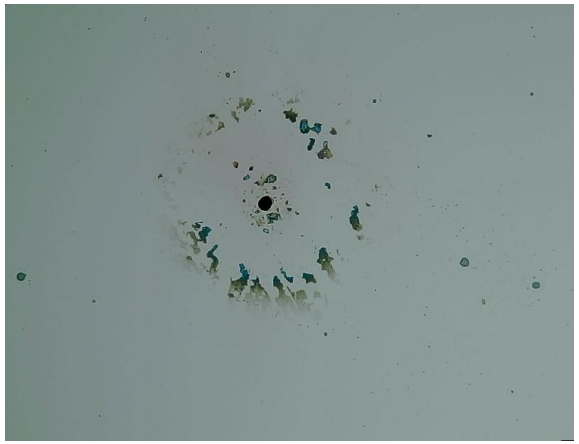
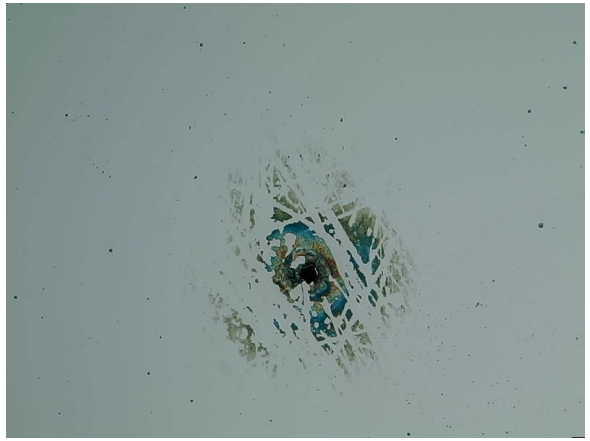
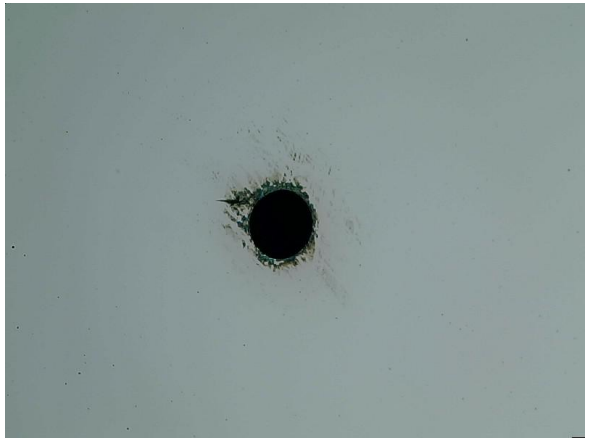




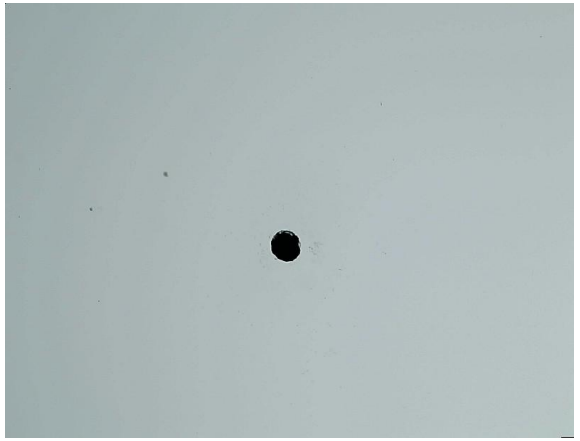
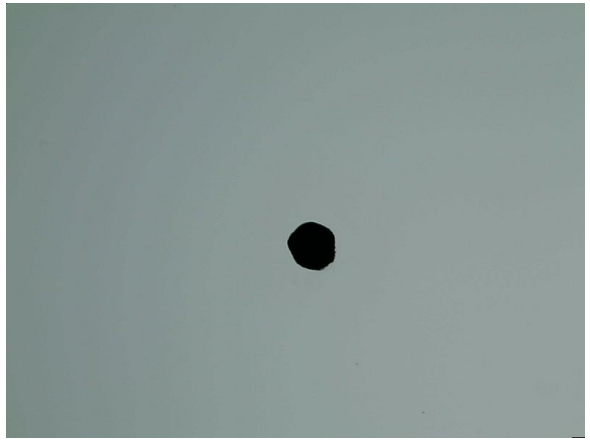
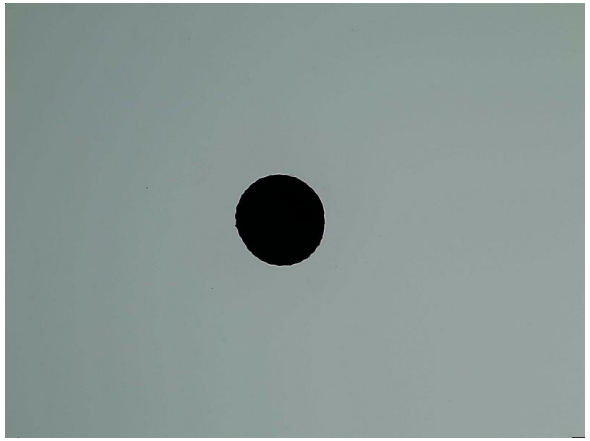
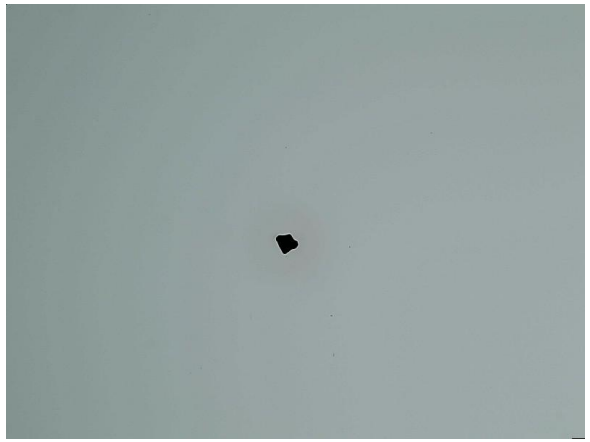
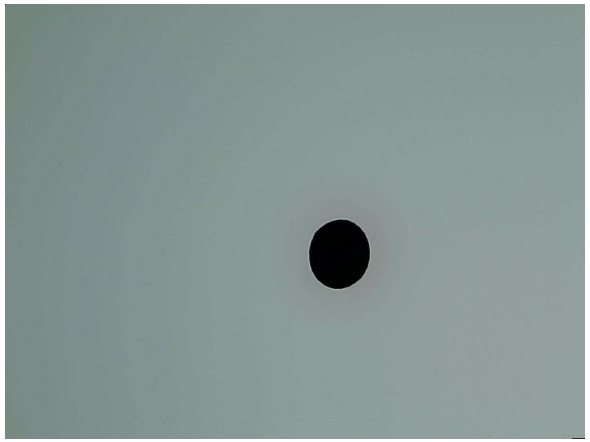


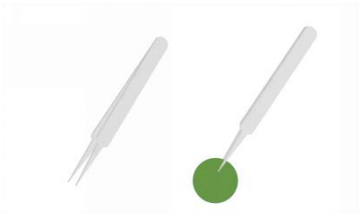
Design	30 (um)	50 (um)	100 (um)
Incident Diameter	28.906	49.61	98.828
Exit Diameter	10.918	15.626	72.656

Before chemical cleaning

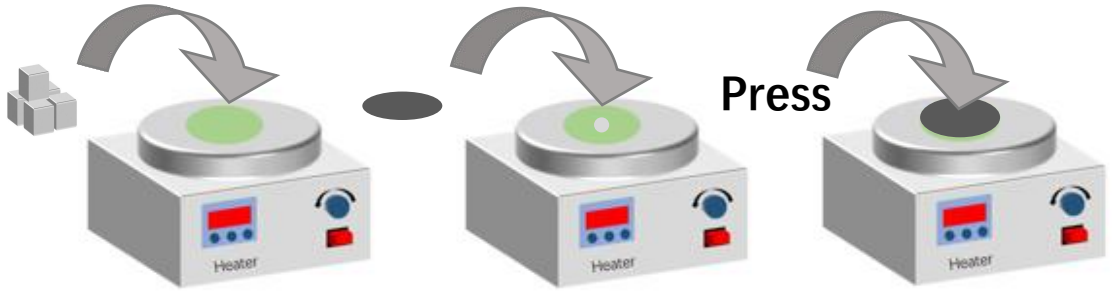
	30 um	50 um	100 um
Incident surface			
Exit surface			

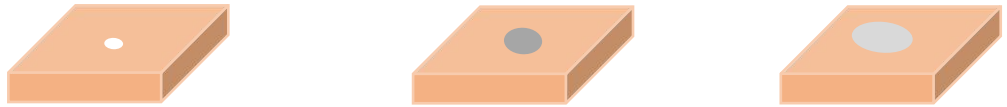
After chemical cleaning

	30 um	50 um	100 um
Incident surface			
Exit surface			



Diameter：100um



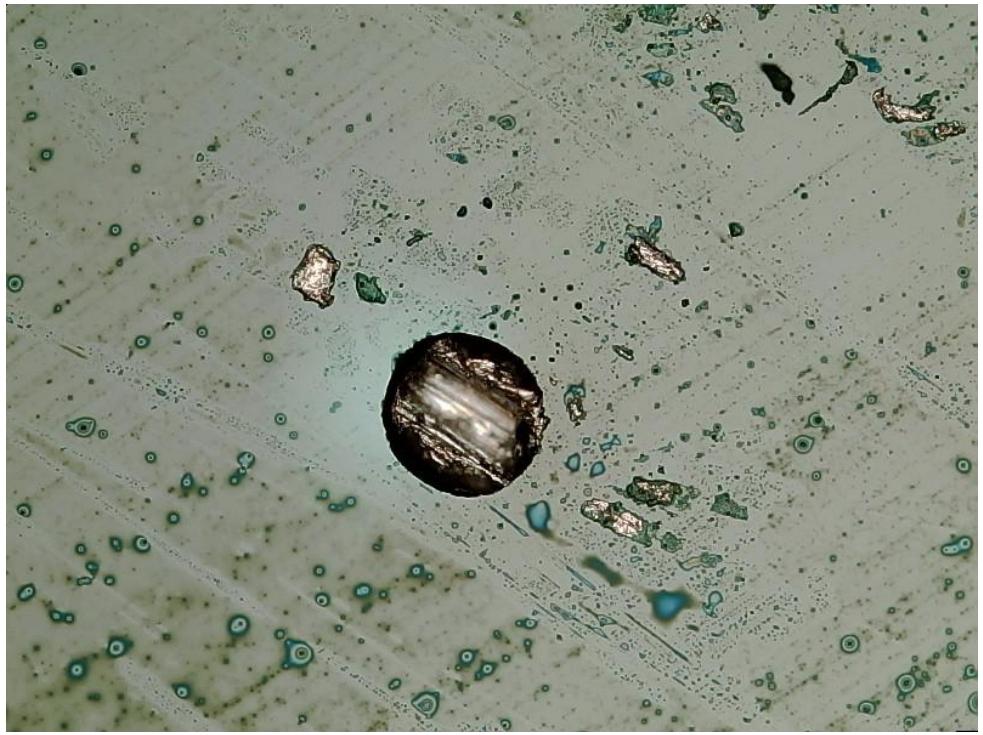




SiC Substrate

Indium

Silicon wafer

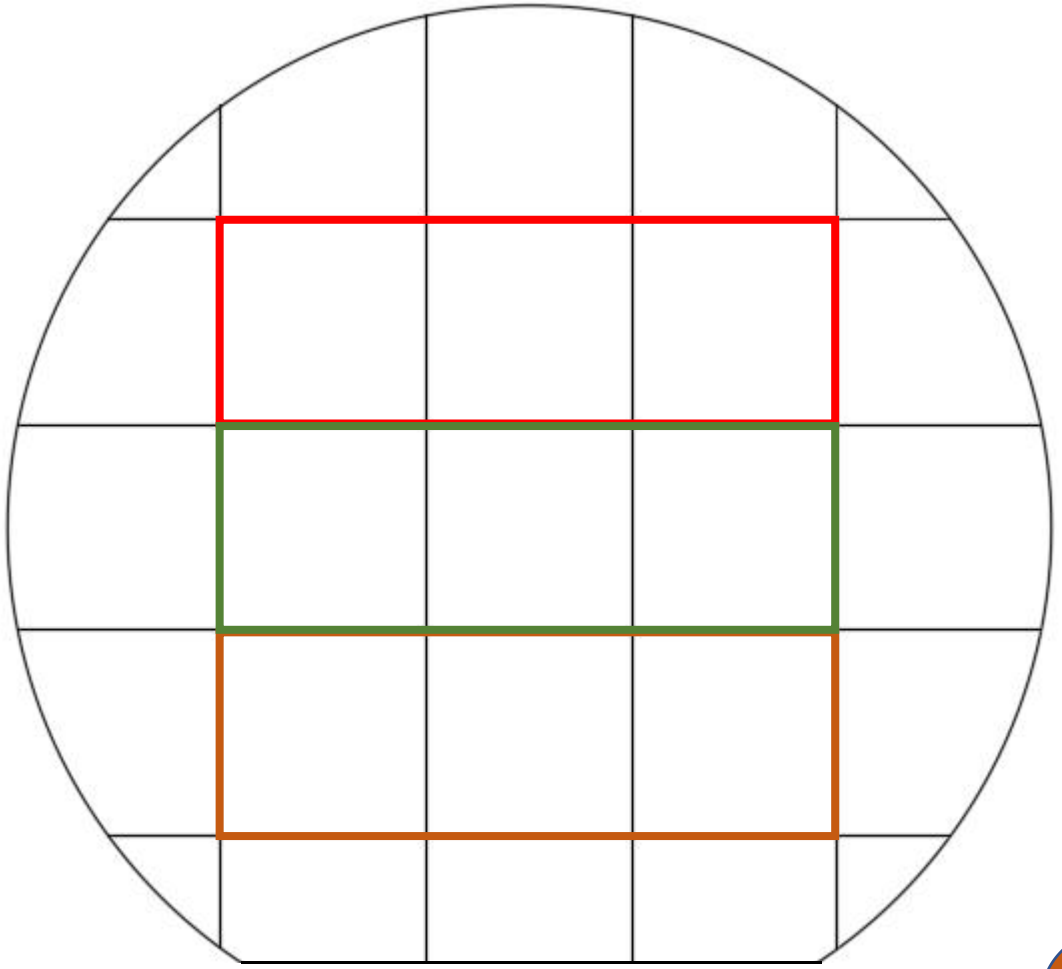


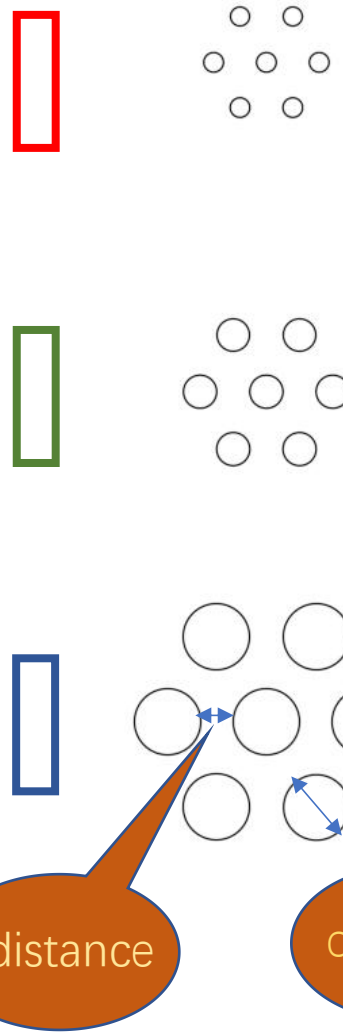
Incident Surface -100um



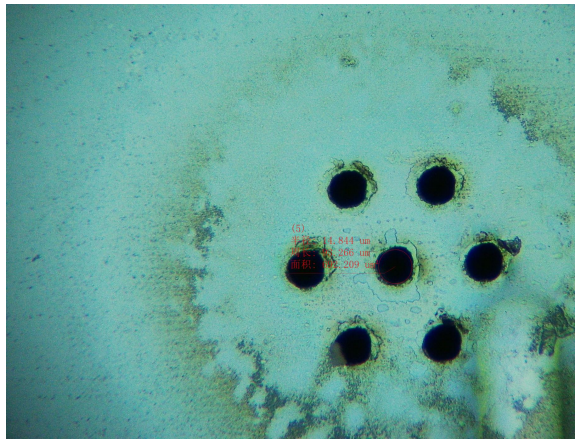
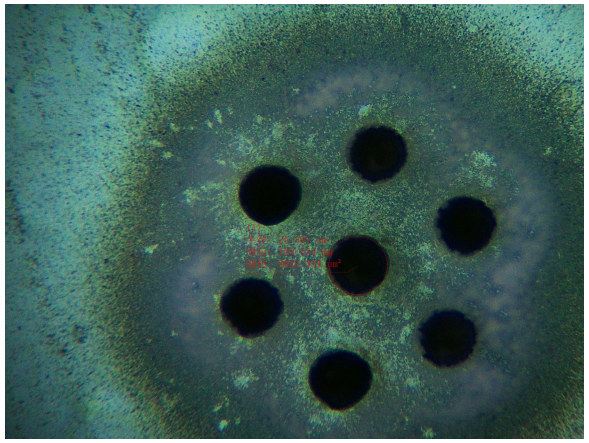
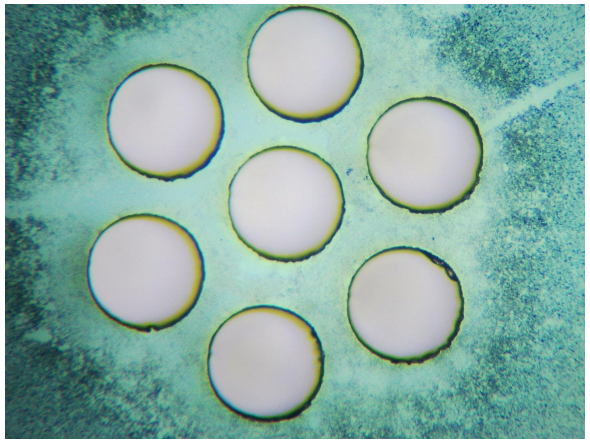
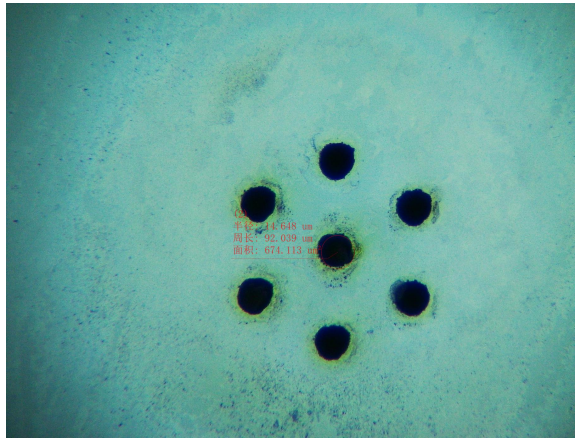
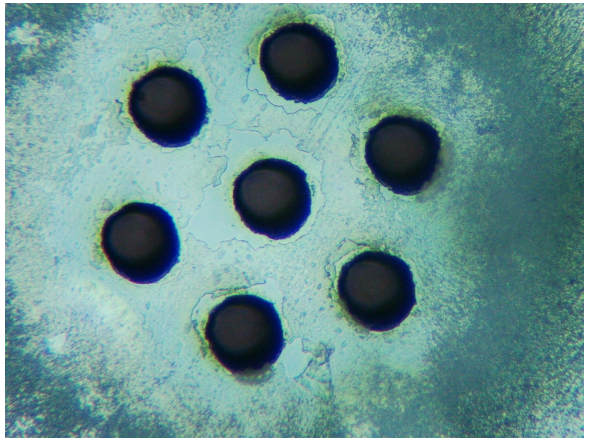
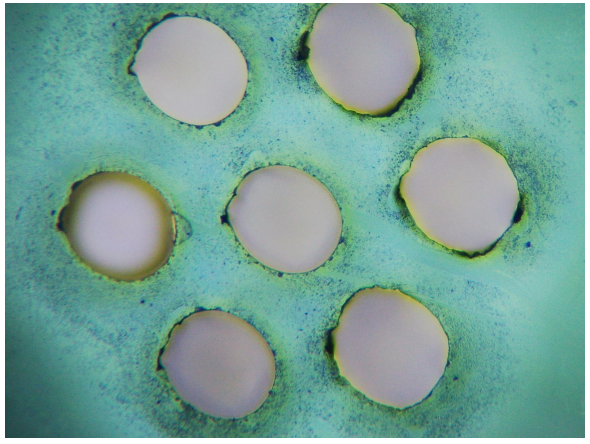
Exit Surface -100um

Second Experiment





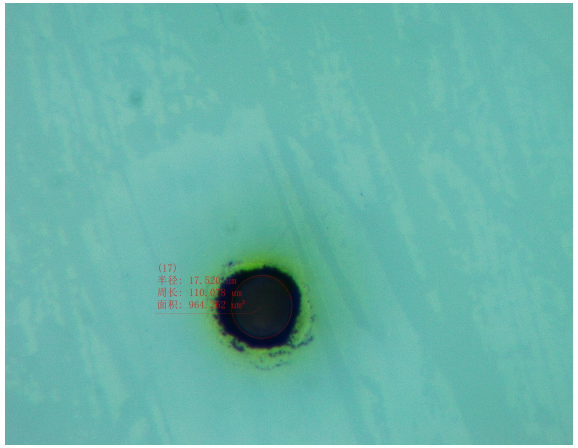
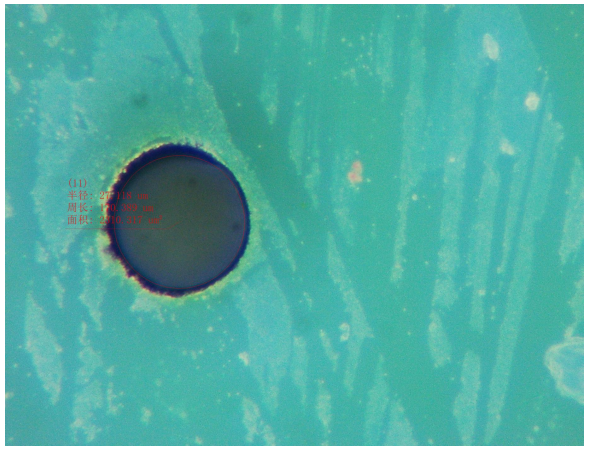
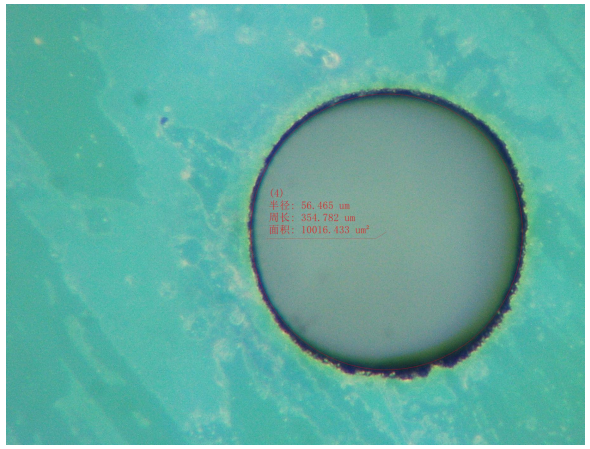
Second Experiment

	30 um	50 um	100 um
Incident surface			
Exit surface			

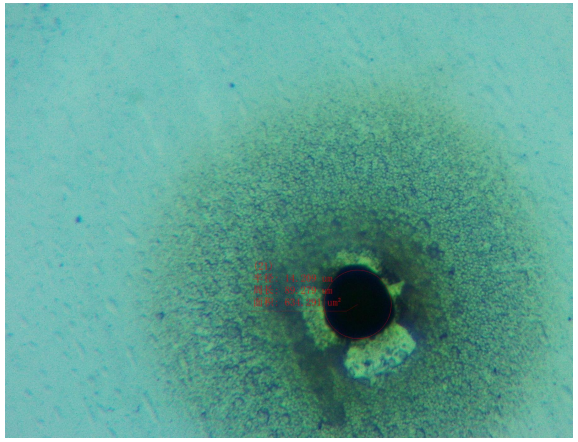
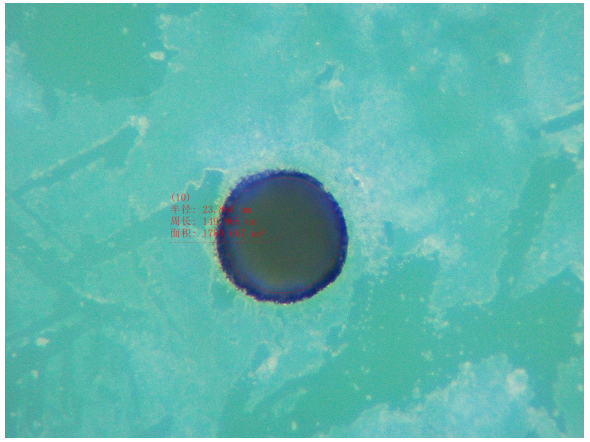
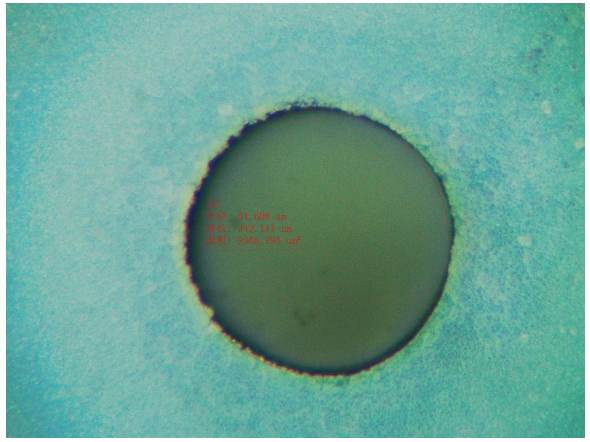
Second Experiment

30 um | 50 um | 100 um

Incident surface

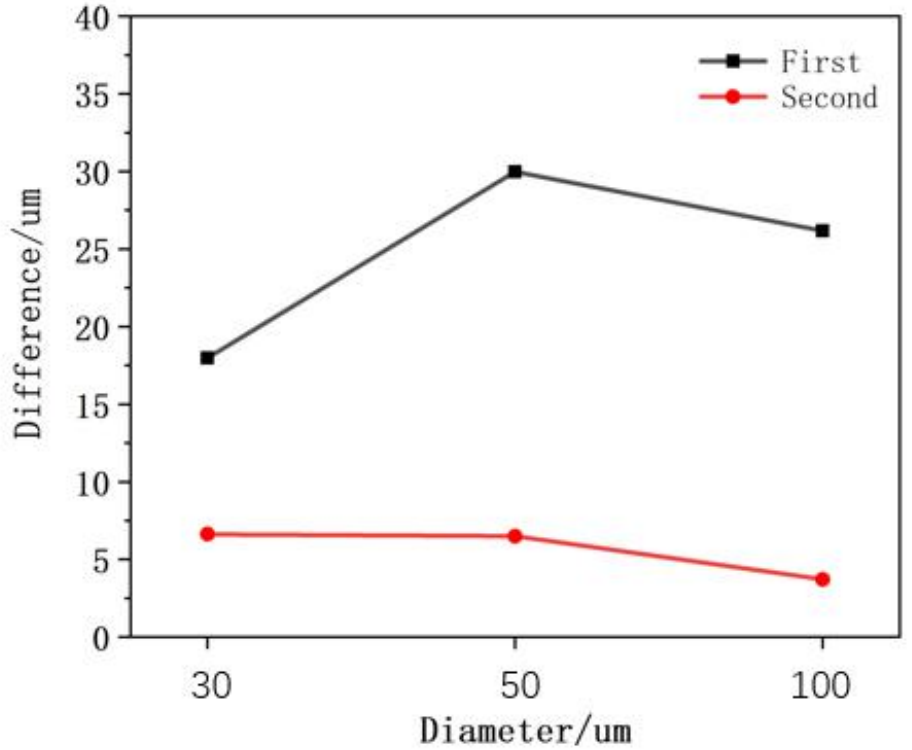




Exit surface

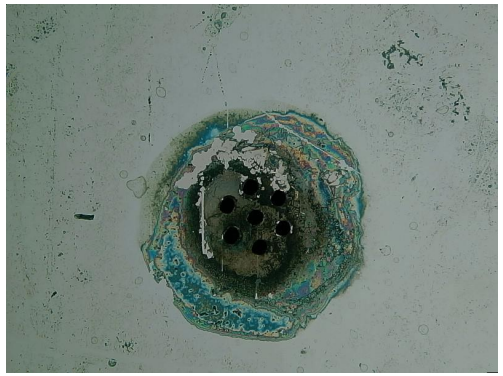
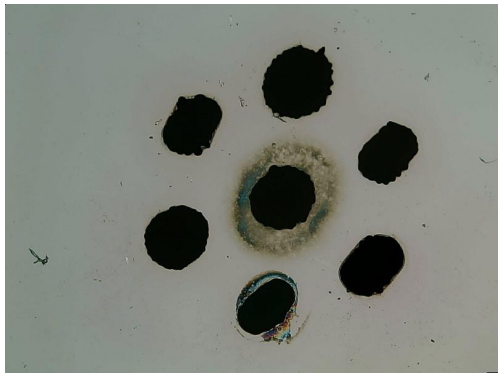




Design	30 (um)	50 (um)	100 (um)
Incident Diameter	35.040	54.236	112.930
Exit Diameter	28.418	47.736	109.216

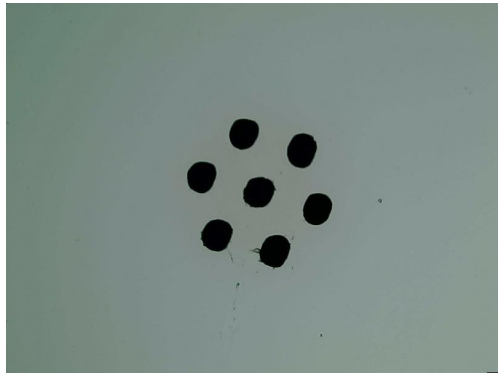
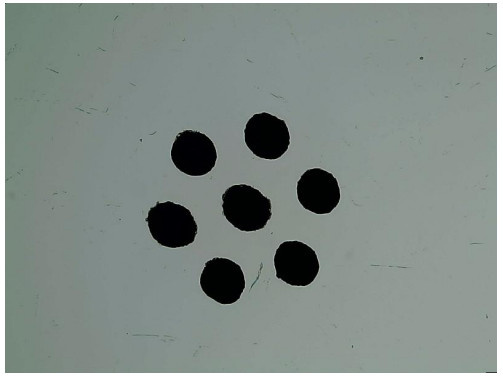
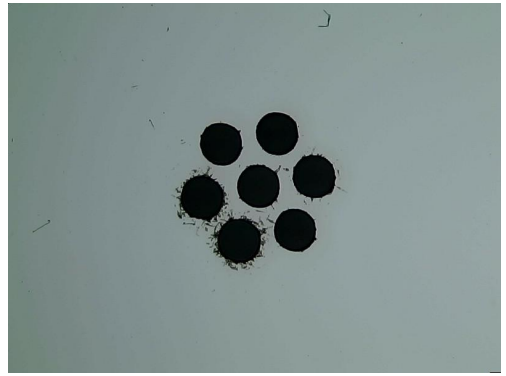
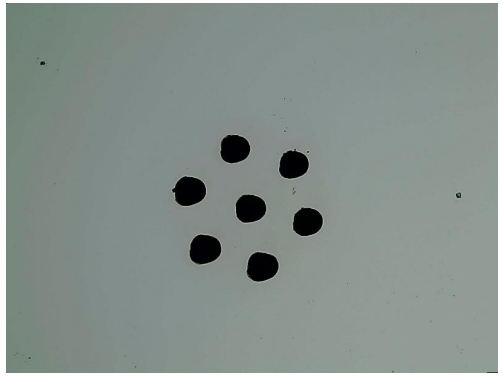
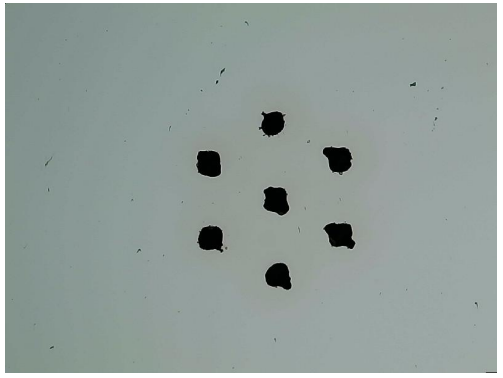
	Design	30 (um)	50 (um)	100 (um)
First Experiment	Incident Diameter	28.906	49.61	98.828
	Exit Diameter	10.918	15.626	72.656
	Difference	17.988	29.984	26.172
Second Experiment	Incident Diameter	35.040	54.236	112.930
	Exit Diameter	28.418	47.736	109.216
	Difference	6.622	6.500	3.714



Before chemical cleaning

	30 um	50 um	100 um
Incident surface			
Exit surface			

After chemical cleaning

	30 um	50 um	100 um
Incident surface			
Exit surface			

宽带隙半导体

谢谢大家

欢迎提出宝贵意见